



### **IXFP5N50P3 Information**



For Reference Only

Part Number IXFP5N50P3

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 500V 5A TO-220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## **Certified Quality**

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# **IXFP5N50P3 Specifications**

Manufacturer         IXFP5N50P3           Manufacturer         IXYS           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         HiPerFET?, Polar3?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         5A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ ImA           Gate Charge (Qg) (Max) @ Vgs         6.9nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         370pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         114W (Tc)           Rds On (Max) @ Id, Vgs         1.65 Ohm @ 2.5A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Sumplier Device Package         TO-220AB		
Category  Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single  TO-220-3  Series HiPerFET?, Polar3?  FET Type N-Channel  Technology MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  1.65 Ohm @ 2.5A, 10V  Operating Temperature  Mounting Type  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  To-220-3  To-	Manufacturer Part Number	IXFP5N50P3
Transistors - FETs, MOSFETs - Single  Package TO-220-3  Series HiPerFET?, Polar3?  FET Type N-Channel Technology MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss) 500V  Current - Continuous Drain (Id) @ 25°C 5A (Tc)  Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 5V @ ImA  Gate Charge (Qg) (Max) @ Vgs 6.9nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds 70pF @ 25V  Vgs (Max)  ### 30V  FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.65 Ohm @ 2.5A, 10V  Operating Temperature Mounting Type Through Hole	Manufacturer	IXYS
PackageTO-220-3SeriesHiPerFET?, Polar3?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 1mAGate Charge (Qg) (Max) @ Vgs6.9nC @ 10VInput Capacitance (Ciss) (Max) @ Vds370pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)114W (Tc)Rds On (Max) @ Id, Vgs1.65 Ohm @ 2.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough Hole	Category	Discrete Semiconductor Products
SeriesHiPerFET?, Polar3?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 1mAGate Charge (Qg) (Max) @ Vgs6.9nC @ 10VInput Capacitance (Ciss) (Max) @ Vds370pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)114W (Tc)Rds On (Max) @ Id, Vgs1.65 Ohm @ 2.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough Hole		Transistors - FETs, MOSFETs - Single
FET Type  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  1.65 Ohm @ 2.5A, 10V  Operating Temperature  - Through Hole	Package	TO-220-3
Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  5A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  1.65 Ohm @ 2.5A, 10V  Operating Temperature  MOSFET (Metal Oxide)  500V  5A (Tc)  5A (Tc)  5A (Tc)  5A (Tc)  5V @ ImA  6.9nC @ 10V  1.0V	Series	HiPerFET?, Polar3?
Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  5A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  10V  Vgs(th) (Max) @ Id  5V @ 1mA  Gate Charge (Qg) (Max) @ Vgs  6.9nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ±30V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  1.65 Ohm @ 2.5A, 10V  Operating Temperature  Mounting Type  Through Hole	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 5A (Tc)  Drive Voltage (Max Rds On, Min Rds On) 10V  Vgs(th) (Max) @ Id 5V @ 1mA  Gate Charge (Qg) (Max) @ Vgs 6.9nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds 370pF @ 25V  Vgs (Max) ±30V  FET Feature -  Power Dissipation (Max) 114W (Tc)  Rds On (Max) @ Id, Vgs 1.65 Ohm @ 2.5A, 10V  Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Through Hole	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  5V @ 1mA  Gate Charge (Qg) (Max) @ Vgs  6.9nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  370pF @ 25V  Vgs (Max)  ET Feature  -  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  1.65 Ohm @ 2.5A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole	Drain to Source Voltage (Vdss)	500V
Vgs(th) (Max) @ Id       5V @ 1mA         Gate Charge (Qg) (Max) @ Vgs       6.9nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       370pF @ 25V         Vgs (Max)       ±30V         FET Feature       -         Power Dissipation (Max)       114W (Tc)         Rds On (Max) @ Id, Vgs       1.65 Ohm @ 2.5A, 10V         Operating Temperature       -55°C ~ 150°C (TJ)         Mounting Type       Through Hole	Current - Continuous Drain (Id) @ 25°C	5A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  770pF @ 25V  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  1.65 Ohm @ 2.5A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  6.9nC @ 10V  370pF @ 25V  14W (Tc)  114W (Tc)  1.65 Ohm @ 2.5A, 10V  Through Hole	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  1.65 Ohm @ 2.5A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole	Vgs(th) (Max) @ Id	5V @ 1mA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)114W (Tc)Rds On (Max) @ Id, Vgs1.65 Ohm @ 2.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough Hole	Gate Charge (Qg) (Max) @ Vgs	6.9nC @ 10V
FET Feature -  Power Dissipation (Max) 114W (Tc)  Rds On (Max) @ Id, Vgs 1.65 Ohm @ 2.5A, 10V  Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Through Hole	Input Capacitance (Ciss) (Max) @ Vds	370pF @ 25V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  1.65 Ohm @ 2.5A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs  1.65 Ohm @ 2.5A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole	FET Feature	-
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$ Mounting Type Through Hole	Power Dissipation (Max)	114W (Tc)
Mounting Type Through Hole	Rds On (Max) @ Id, Vgs	1.65 Ohm @ 2.5A, 10V
	Operating Temperature	-55°C ~ 150°C (TJ)
Supplier Device Package TO-220AR	Mounting Type	Through Hole
Supplier Device Luciage 10 220/10	Supplier Device Package	TO-220AB
Package / Case TO-220-3	Package / Case	TO-220-3
Report errors?		Report errors?

#### **IXFP5N50P3** Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## **IXFP5N50P3 Payment Methods**



















### **IXFP5N50P3 Shipping Methods**













If you have any question about IXFP5N50P3, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com